L Number	Hits	Search Text	DB	Time stamp
155	2447	@ad<=20030922 and (257/750-752).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 09:03
156	1757	@ad<=20030922 and (257/753-756).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 09:05
157	3767	@ad<=20030922 and (257/757-760).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 09:06
160	1886	@ad<=20030922 and (257/773).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 09:07
161	126	@ad<=20030922 and 'dielectric constant' with 'SiOC'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 09:15
165	7	@ad<=20030922 and 'conductive plug' with 'Cu' with 'W' with 'silicide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 09:31
166	138	@ad<=20030922 and 'conductive' with 'Cu' with 'W' with 'silicide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 09:18
167	1	@ad<=20030922 and 'interconnect' same 'conductive' with 'Cu' with 'W' with 'silicide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 09:19
168	12	@ad<=20030922 and 'interconnection' same 'conductive' with 'Cu' with 'W' with 'silicide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 09:19
169	36	@ad<=20030922 and 'interconnection' same 'substrate' with 'Silicon' with 'silicon germanium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 09:32
-	1705	@ad<=20020607 and (257/773).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 11:42
-	4488	@ad<=20020607 and (438/622-624).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 09:09
-	557	@ad<=20020607 and (438/629).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 11:42
-	1623	@ad<=20020607 and (438/637).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 11:42

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-	545	@ad<=20020607 and (438/631).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 11:42
-	0	@ad<=20020607 and 'interconnection' and 'IDL' with 'SiOC' and 'insulating' with 'SiC'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:22
-	0	@ad<=20020607 and 'interconnection' and 'IDL' same 'SiOC' with 'SiC'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/10 10:43
-	0	@ad<=20020607 and 'interconnection' and 'SiOC' same 'SiC' same 'USG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/10 10:43
-	23	@ad<=20020607 and 'interconnection' and 'SiOC' same 'SiC'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:34
-	1	@ad<=20020607 and 'dielectric' same 'SiOC' same 'undoped silicate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/10 10:50
-	28	@ad<=20020607 and 'dielectric' same 'SiOC' same 'SiC'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 09:57
-	2	@ad<=20020607 and 'dielectric' same 'SiOC' same 'SiC' same 'PSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/10 12:12
-	1	@ad<=20020607 and 'dielectric' same 'SiOC' same 'SiC' same 'USG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/10 12:13
-	0	@ad<=20020607 and 'interconnection' and 'SiOC' same 'USG' same 'SiN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/26 17:40
-	26	@ad<=20020607 and 'interconnection' and 'SiOC' same 'SiC'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/26 17:39
-	2	@ad<=20020607 and 'interconnection' and 'SiOC' and 'USG' and 'SiN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/26 17:45
-	15	@ad<=20020607 and 'interconnection' and 'SiOC' same 'SiC' and 'SiN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/26 17:45
-	28	@ad<=20020607 and 'low k' same 'silicon oxide' same 'SiN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/09 14:34

-	969	@ad<=20020607 and (257/750).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 11:43
-	2856	@ad<=20020607 and (257/758-760).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 11:44
-	1737	@ad<=20020607 and (257/773).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 11:45
-	4552	@ad<=20020607 and (438/622-624).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 11:47
-	564	@ad<=20020607 and (438/629).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 11:47
-	1664	@ad<=20020607 and (438/637).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 11:49
-	548	@ad<=20020607 and (438/631).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/27 11:49
-	2	"20030227087"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/09 13:41
-	86	@ad<=20020607 and 'hard mask' same 'SiN' with 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 12:22
-	39	@ad<=20020607 and 'hard mask' same 'SiN' with 'SiC'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/09 14:36
-	18	@ad<=20020607 and 'low k' same 'hard mask' same 'SiN' with 'SiC'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/09 14:36
-	2	@ad<=20020607 and 'MSQ' same 'hard mask' same 'SiN' with 'SiC'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:43
-	5	@ad<=20020607 and 'MSQ' same 'SiN' with 'SiC'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/09 14:59
-	19	@ad<=20020607 and 'hard mask' same 'SiC' with 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 12:23

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-	2	@ad<=20020607 and 'hard mask' same 'SiC' with 'TEOS'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 13:41
-	17	@ad<=20020607 and 'etch stop' with 'SiC' with 'SiO.sub.2'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 13:42
-	2	@ad<=20020607 and 'MSQ' same 'etch stop' with 'SiC' with 'SiO.sub.2'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 13:42
-	4	"6677183"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:38
-	649	@ad<=20020607 and 'interconnection' same 'tungsten' with 'copper' same' low k' same 'etch stop' with 'SiC'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:25
-	31	@ad<=20020607 and 'interconnection' same 'tungsten plug' with 'copper' same' low k' same 'etch stop' with 'SiC' same 'USG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:30
-	90	@ad<=20020607 and 'tungsten copper' same 'interconnection'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:32
-	0	@ad<=20020607 and 'tungsten copper' same 'interconnection' and 'low k' and 'SiC'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:32
-	17	@ad<=20020607 and 'tungsten copper' same 'interconnection' and 'etch stop'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:32
-	0	@ad<=20020607 and 'interconnection' and 'USG' same 'SiC' same 'low k'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:35
-	7	@ad<=20020607 and 'interconnection' and 'USG' and 'SiC' and 'low k'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:35
-	12	@ad<=20030922 and 'interconnection' and 'USG' and 'SiC' and 'low k'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:35
-	1	"6312793".PN.	USPAT	2004/10/31 08:39
-	1	"6303523".PN.	USPAT	2004/10/31 08:40
-	1	"6238751".PN.	USPAT	2004/10/31 08:40
-	1	"6147009".PN.	USPAT	2004/10/31 08:40
-	1	"6072227".PN.	USPAT	2004/10/31 08:40
-	1	"6054379".PN.	USPAT	2004/10/31 08:40

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-	1	"6001747".PN.	USPAT	2004/10/31 08:41
-	1	"5989998".PN.	USPAT	2004/10/31 08:41
-	2	@ad<=20020607 and 'USG' same 'hard mask' same 'low dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:46
-	270	@ad<=20020607 and 'dielectric' same 'hard mask' same 'low dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:58
-	24	@ad<=20020607 and 'interconnection' same 'dielectric' same 'hard mask' same 'low dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:53
-	4	(("6465867") or ("6016000")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:55
-	2	"20010045651"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:55
-	190	@ad<=20020607 and 'dielectric' same 'SiC' same 'low dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:59
-	56	@ad<=20020607 and 'dielectric' same 'SiC' same 'low dielectric' same 'barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 07:19
-	34	@ad<=20020607 and 'dielectric' same 'SiC' same 'low-k' same 'barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 08:59

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